



#### N-CHANNEL ENHANCEMENT MODE MOSFET

### **Product Summary**

BV <sub>DSS</sub>	R <sub>DS(ON)</sub>	I <sub>D</sub> T <sub>A</sub> = +25°C
30V	5Ω @ V <sub>GS</sub> = 4V	200mA
307	$7\Omega$ @ $V_{GS} = 2.5V$	115mA

## **Description and Applications**

This MOSFET is designed to meet the stringent requirements of automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

- Brushless DC Motor Control
- DC-DC Converters
- Load Switch

### **Features**

- N-Channel MOSFET
- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Small Surface Mount Package
- ESD Protected Gate 2KV
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- The DMN33D8LTQ is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF 16949 certified facilities.

https://www.diodes.com/quality/product-definitions/

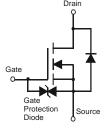
### **Mechanical Data**

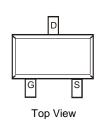
- Case: SOT523
- Case Material: Molded Plastic. "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish Annealed Over Alloy 42 Leadframe (Lead Free Plating). Solderable per MIL-STD-202, Method 208@3
- Terminal Connections: See Diagram
- Weight: 0.002 grams (Approximate)





Top View





**Equivalent Circuit** 

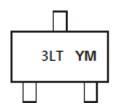
### **Ordering Information** (Note 4)

Part Number	Case	Packaging
DMN33D8LTQ-7	SOT523	3,000/Tape & Reel
DMN33D8LTQ-13	SOT523	10,000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/

## **Marking Information**



3LT = Product Type Marking Code YM = Date Code Marking Y = Year (ex: H = 2020) M = Month (ex: 9 = September)

Date Code Key

Year	2018	2019	2020	2021	2022	2023	2024	2025	2026	2027	2028	2029
Code	F	G	Н		J	K	Ш	М	Ν	0	Р	R
Mandh			N4	A				A	0	•		
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec



# **Maximum Ratings** (@ $T_A = +25^{\circ}C$ , unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Drain-Source Voltage		VDSS	30	V
Gain-Source Voltage		V <sub>GSS</sub>	±20	V
Drain Current (Note 5)	Continuous	lp	115	mA

# Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	P <sub>D</sub>	240	mW
Thermal Resistance, Junction to Ambient (Note 5)	RθJA	521	°C/W
Total Power Dissipation (Note 6)	PD	300	mW
Thermal Resistance, Junction to Ambient (Note 6)	RθJA	420	°C/W
Operating and Storage Temperature Range	TJ, TSTG	-55 to +150	°C

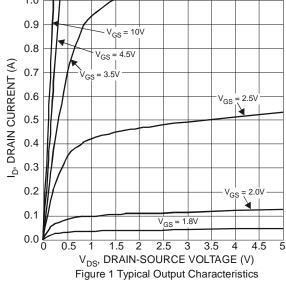
## **Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

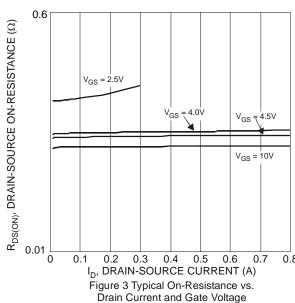
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition		
OFF CHARACTERISTICS (Note 7)								
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	30	_	_	V	$V_{GS} = 0V, I_D = 250\mu A$		
Zero Gate Voltage Drain Current	I <sub>DSS</sub>		_	1.0	μΑ	V <sub>DS</sub> = 30V, V <sub>GS</sub> = 0V		
Gate-Body Leakage	Igss		_	±10	μΑ	V <sub>G</sub> S = ±20V, V <sub>D</sub> S = 0V		
ON CHARACTERISTICS (Note 7)								
Gate Threshold Voltage	Vgs(TH)	0.8	_	1.5	V	$V_{DS} = 3V, I_{D} = 100\mu A$		
Static Drain-Source On-Resistance	Danie		_	5	Ω	V <sub>G</sub> S = 4V, I <sub>D</sub> = 10mA		
Static Drain-Source On-Resistance	RDS(ON)		_	7	Ω	V <sub>G</sub> S = 2.5V, I <sub>D</sub> = 5mA		
Diode Forward Voltage	VsD	_	_	1.2	V	V <sub>G</sub> S = 0V, I <sub>S</sub> = 115mA		
DYNAMIC CHARACTERISTICS (Note 8)								
Input Capacitance	Ciss		48					
Output Capacitance	Coss		11		pF	V <sub>DS</sub> = 5V, V <sub>GS</sub> = 0V, f = 1.0MHz		
Reverse Transfer Capacitance	Crss	_	8	_				
Total Gate Charge (V <sub>GS</sub> = 4.5V)	Qg	_	0.55	_				
Total Gate Charge (V <sub>GS</sub> = 10V)	Qg		1.23	_	nC	Vgs = 10V, Vps = 10V,		
Gate-Source Charge	Qgs		0.14		nc nc	ID = 250mA		
Gate-Drain Charge	$Q_{gd}$		0.14					
Turn-On Delay Time	t <sub>D</sub> (ON)		2.9	_				
Turn-On Rise Time	tR		2.6	_	ns	V <sub>DD</sub> = 30V, I <sub>D</sub> = 0.2A, V <sub>GEN</sub> = 10V,		
Turn-Off Delay Time	tD(OFF)		18.2		115	$R_{GEN} = 25\Omega$		
Turn-Off Fall Time	tF		13.6	_				

 Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
Short duration pulse test used to minimize self-heating effect. Notes:

<sup>8.</sup> Guaranteed by design. Not subject to product testing.







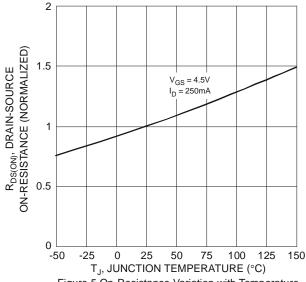
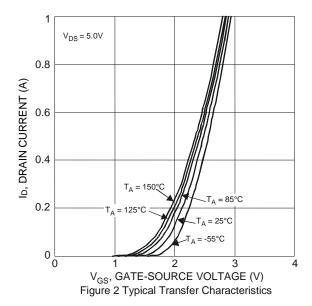


Figure 5 On-Resistance Variation with Temperature



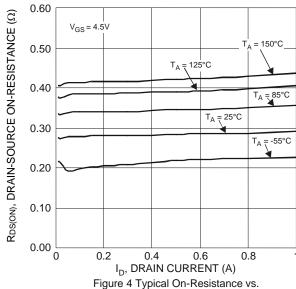


Figure 4 Typical On-Resistance vs. Drain Current and Temperature

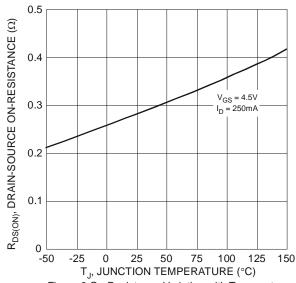


Figure 6 On-Resistance Variation with Temperature



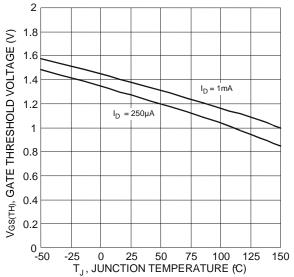
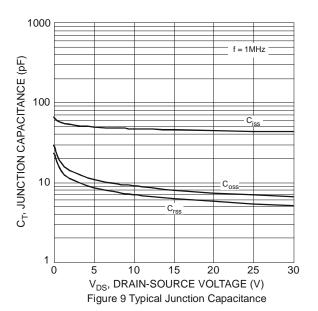
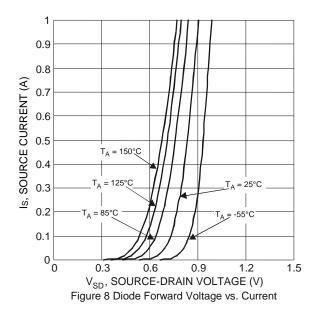
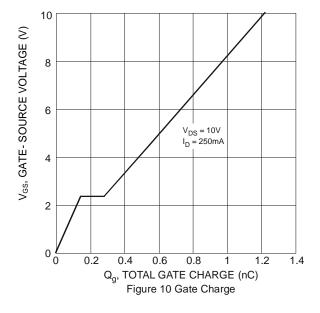


Figure 7 Gate Threshold Variation vs. Junction Temperature





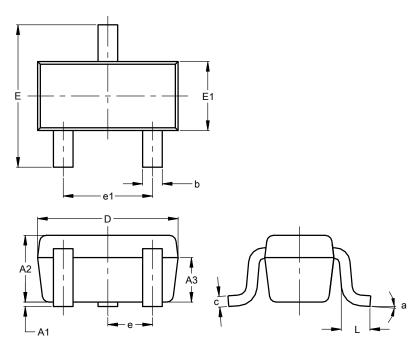




## **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### **SOT523**

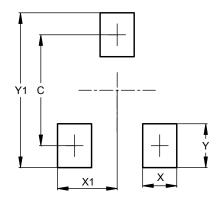


SOT523							
Dim	Min	Max	Тур				
A1	0.00	0.10	0.05				
A2	0.60	0.80	0.75				
A3	0.45	0.65	0.50				
b	0.15	0.30	0.22				
С	0.10	0.20	0.12				
D	1.50	1.70	1.60				
Е	1.45	1.75	1.60				
E1	0.75	0.85	0.80				
е	0.50 BSC						
e1	0.90	1.10	1.00				
L	0.20	0.40	0.33				
а	0°		8°				
All Dimensions in mm							

# **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### **SOT523**



Dimensions	Value (in mm)		
С	1.29		
Х	0.40		
X1	0.70		
Y	0.51		
Y1	1.80		



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